



KIT TA Status

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The infrastructure



- Description on <u>http://www.ekp.kit.edu/english/irradiation_center.php</u>
- Cyclotron parameters:
 - Proton energy

~23 MeV (25.3MeV at extraction) ~2.0µA (100nA - 20µA)

- Proton current
- Max. object width 44cm
- Max. object height 17cm
- N₂-cooling temperature -30°C
- On average 4-5h slot every second week
 - up to 6 weeks turn-around time
- E.g., irradiating one sensor of 20mm x 20mm to 5x10¹⁵ n_{1MeV}/cm² takes about 90 minutes.
- Min. quantity of access to be provided: 100h beam time
- Samples can be shipped to us, we irradiated and send them back
 - No visitors expected!

Initial contact and infos: <u>irradiations@lists.kit.edu</u>

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Projects so far



ect Access Units
5 2.13
5 0.42
015 2.62
5.99
2.92
016 1.22
016 5.43
7 1.67
016 0.17
016 2.62
016 1.92
016 4.08
0.08
1.73
0.33
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Total: 16 projects, 53 users, 33.33h







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Publicity

- Dedicated web page
- Link to AIDA TA on RD50 web page
- Listed in http://irradiationfacilities.web.cern.ch/publicDB.php
- TA video online
- Presentation at the 4th Beam Telescopes and Test Beams Workshop 2016 (3.2.2016, Orsay) with 60 participants
- Personal reminders to previous customers



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Upgraded monitoring



- Rare SEU in controller memory generate random changes in scanning pattern
- Detailed logging of scanning available now
 - alarm issued when deviations from expectation arise
- Working on online monitoring of beam current for fast feedback





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5.4.2017



TWO EXAMPLES OF PROJECTS

Irradiation study of the CMS upgrade pixel detector readout chip

- AIDA-2020-KIT-2015-04
- PROC600 designed for 600MHz/cm²
- To be confirmed after irradiation
- Publication: 2017 JINST 12 C01078
- 23MeV protons
 300kGy / 10¹⁴p/cm² in SiO₂
- Rate capability maintained after 1.2MGy



Figure 5. Efficiency of PROC600 before and after irradiation.

CMS tracker upgrade: front-side biasing with IFX sensor



- AIDA-2020-KIT-2016-02
- Evaluation of front-side biasing for strip sensors at HL-LHC, which would very much simplify module assembly
- Edge resistivity increases dramatically for high fluence (>6x10¹⁴n_{eq}/cm²)
 → not useful for HL-LHC due to large voltage drop and power dissipation
- Publication in preparation



Sample	Fluence (neq/cm2)	Annealing
VE525852_03_Irrad	6.07E14	10 min @ 60°C
VE525852_04_Irrad	6.07E14	10 min @ 60°C
VE525852_07_Baby	6.82E14	10 min @ 60°C
VE525852_12_Baby	2.10E15	10 min @ 60°C
VE525852_15_Baby	6.82E14	10 min @ 60°C
VE525852_17_Baby	2.10E15	10 min @ 60°C
VE525852_19_Baby	6.82E14	0 min @ start





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Conclusion

- Irradiations running smoothly
- Upgrading control system
- Slightly behind AIDA schedule
- Very tedious to find/get publications from users

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SPARES

Energy at Target

- 25.3MeV is the energy in the beam line
- Protons have to pass several materials until they hit the samples
- SRIM gives us a proton energy entering the samples of about 23.8MeV and on average in the sample: **22.9MeV**
- Samples covered by Nickel foils see lower energy ~22.8MeV



01/06/10 16. RD50 Workshop

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IFK

Karlsruhe Institute of Technology

Calibration with Diodes

- 3 ELMA diodes from HH
 - Diode 03: U_{dep} = 44V, I_{dep} = 0.2nA, I(2*U_{dep})= 5nA, V=0.25cm^2 x 374 \mu m = 9.36e-3cm^3
 - Diode 06: $U_{dep} = 46V$, $I_{dep} = 2nA$, $I(2*U_{dep}) = 5nA$, V=0.25cm² x 375µm = 9.37e-3cm³
 - Diode 08: U_{dep} = 45V, I_{dep} = 0.2nA, I(2*U_{dep})= 0.4nA, V=0.25cm^2 x \ 374 \mu m = 9.36e-3cm^3
- Irradiation with $I_{beam} = 1.04 \mu A$, $v_x = 115 \text{ mm/s}$, $n_{scans} = 5$
 - F_{est} = (0.56 ± 0.06)e14 p/cm²
- Ni-foils:
 - F_{Ni} = (0.60 ± 0.07)e14 p/cm²



Calibration with Diodes



- Specific leakage currents after irradiation:
 - Diode 03: $I(2xU_{dep}) = 46.2\mu A$, $\Delta I/V = 4.925e-3 A/cm^3$
 - Diode 06: $I(2xU_{dep}) = 45.8\mu A$, $\Delta I/V = 4.888e-3 A/cm^3$
 - Diode 08: $I(2xU_{dep}) = 46.3\mu A$, $\Delta I/V = 4.947e-3 A/cm^3$
- Including a 1°C error for temperature measurement we get $\Delta I/V = (4.9 \pm 0.5)e-3 A/cm^3$
- And finally with $\alpha = 3.99 \pm 0.3e-17 \text{ A/cm}^2$ at 20°C after annealing for 80min at 60°C: $\mathbf{F}_{diode} = (4.9 \pm 0.5)e-3 \text{ A/cm}^3 / \alpha = (1.23 \pm 0.22)e14 n_{eq}/cm^2$



Hardness Factor к

- The hardness factor could be derived by $\kappa = F_{diode}/F_{Ni} = 2.05\pm0.61$
- Previous assumption was **1.85** for **26MeV** protons
- Hardness factor was derived from simulated NIEL data by Huhtinen¹
- Assuming about 22.9 MeV protons on average in the sample, we get κ = 2.00±??
- Alternative measurements of NIEL show quite a spread...



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¹ M. Huhtinen, "Simulation of non-ionising energy loss and defect formation in silicon", NIM A 491 (2002) 194-215

Considering the Errors

- With the used value of 1.85 one still gets an agreement of the equivalent fluence from the different methods considering the errors !
- Considering the nice agreement of measured hardness factor and derived hardness factor from NIEL simulation one could claim the hardness factor for our protons to be **me**



factor for our protons to be **more like 2.0** (+10% to prev. value).

• In general, the stated fluence is **not better than 20%** !

